

Mickaël Lozac'h

List of Publications by Year in descending order

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606
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| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Passivating antireflection coating of crystalline silicon using i/n a-Si:H/SiN trilayer. Journal of Physics and Chemistry of Solids, 2021, 156, 110127. | 1.9 | 9 |
| 2 | Double-sided TOPCon solar cells on textured wafer with ALD SiOx layer. Solar Energy Materials and Solar Cells, 2020, 207, 110357. | 3.0 | 39 |
| 3 | Tuning the Bandgap Character of Quantum-Confined Si-Sn Alloyed Nanocrystals. Advanced Functional Materials, 2020, 30, 1907210. | 7.8 | 5 |
| 4 | Role of silicon surface, polished ~100% and ~111% or textured, on the efficiency of double-sided TOPCon solar cells. Progress in Photovoltaics: Research and Applications, 2020, 28, 1001-1011. | 4.4 | 21 |
| 5 | Hydrogen passivation effect on p-type poly-Si/SiOx stack for crystalline silicon solar cells. AIP Conference Proceedings, 2019, . . | 0.3 | 2 |
| 6 | Near-Surface [Ga]/([In]+[Ga]) Composition in Cu(In,Ga)Se ₂ Thin-Film Solar Cell Absorbers: An Overlooked Material Feature. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800856. | 0.8 | 6 |
| 7 | Roles of hydrogen atoms in p-type Poly-Si/SiO _x passivation layer for crystalline silicon solar cell applications. Japanese Journal of Applied Physics, 2019, 58, 050915. | 0.8 | 12 |
| 8 | Semiconducting silicon-tin alloy nanocrystals with direct bandgap behavior for photovoltaic devices. Materials Today Energy, 2018, 7, 87-97. | 2.5 | 15 |
| 9 | Significant Carrier Extraction Enhancement at the Interface of an InN/p-GaN Heterojunction under Reverse Bias Voltage. Nanomaterials, 2018, 8, 1039. | 1.9 | 6 |
| 10 | Zero-dimensional perovskite-like (CH ₃ NH ₃) ₃ Bi ₂ I ₉ thin films for photovoltaics. , 2018, . . | | 0 |
| 11 | Passivation property of ultrathin SiOx:H / a-Si:H stack layers for solar cell applications. Solar Energy Materials and Solar Cells, 2018, 185, 8-15. | 3.0 | 37 |
| 12 | (Invited) Microplasmas Technologies for Engineering of Silicon Based Quantum Dot Solar Cells. ECS Transactions, 2017, 77, 1-8. | 0.3 | 3 |
| 13 | Bandgap Engineering in OH-Functionalized Silicon Nanocrystals: Interplay between Surface Functionalization and Quantum Confinement. Advanced Functional Materials, 2017, 27, 1701898. | 7.8 | 15 |
| 14 | Stable ultrathin surfactant-free surface-engineered silicon nanocrystal solar cells deposited at room temperature. Energy Science and Engineering, 2017, 5, 184-193. | 1.9 | 11 |
| 15 | Zero-dimensional methylammonium iodo bismuthate solar cells and synergistic interactions with silicon nanocrystals. Nanoscale, 2017, 9, 18759-18771. | 2.8 | 25 |
| 16 | Environmentally Friendly Processing Technology for Engineering Silicon Nanocrystals in Water with Laser Pulses. Journal of Physical Chemistry C, 2016, 120, 18822-18830. | 1.5 | 23 |
| 17 | Enhanced Conversion Efficiency of Hybrid Solar Cells by using Alloyed Silicon-Tin Nanocrystals via Quantum Confinement Effect. , 2014, . . | | 0 |
| 18 | Fabrication of transparent conducting polymer/GaN Schottky junction for deep level defect evaluation under light irradiation. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 470-473. | 0.8 | 8 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | p-Type a-Si:H/ZnO:Al and $\frac{1}{4}$ c-Si:H/ZnO:Al Thin-Film Solar Cell Structures – A Comparative Hard X-Ray Photoelectron Spectroscopy Study. IEEE Journal of Photovoltaics, 2013, 3, 483-487. | 1.5 | 4 |
| 20 | Vacancy-type defects in $\text{In}_x\text{Ga}_{1-x}\text{N}$ grown on GaN templates probed using monoenergetic positron beams. Journal of Applied Physics, 2013, 114, . | 1.1 | 15 |
| 21 | Determination of the surface band bending in $\text{In}_x\text{Ga}_{1-x}\text{N}$ films by hard x-ray photoemission spectroscopy. Science and Technology of Advanced Materials, 2013, 14, 015007. | 2.8 | 11 |
| 22 | Point defects introduced by InN alloying into $\text{In}_x\text{Ga}_{1-x}\text{N}$ probed using a monoenergetic positron beam. Journal of Applied Physics, 2013, 113, 123502. | 1.1 | 7 |
| 23 | The silicon/zinc oxide interface in amorphous silicon-based thin-film solar cells: Understanding an empirically optimized contact. Applied Physics Letters, 2013, 103, . | 1.5 | 12 |
| 24 | Study of Defect Levels in the Band Gap for a Thick InGaN Film. Japanese Journal of Applied Physics, 2012, 51, 121001. | 0.8 | 6 |
| 25 | Study of Defect Levels in the Band Gap for a Thick InGaN Film. Japanese Journal of Applied Physics, 2012, 51, 121001. | 0.8 | 12 |
| 26 | Photocapacitance spectroscopy study of deep-level defects in freestanding n-GaN substrates using transparent conductive polymer Schottky contacts. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, . | 0.6 | 6 |
| 27 | Deep-Level Characterization of Free-Standing HVPE-grown GaN Substrates Using Transparent Conductive Polyaniline Schottky Contacts. Materials Research Society Symposia Proceedings, 2011, 1309, 97. | 0.1 | 0 |
| 28 | Valence band structure of III-V nitride films characterized by hard X-ray photoelectron spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1903-1905. | 0.8 | 6 |
| 29 | Phase Separation Resulting from Mg Doping in p-InGaN Film Grown on GaN/Sapphire Template. Applied Physics Express, 2010, 3, 111004. | 1.1 | 29 |